

Data sheet acquired from Harris Semiconductor SCHS197

August 1997

# *CD74HC4002*

# High Speed CMOS Logic Dual 4-Input NOR Gate

## Features

- Typical Propagation Delay = 8ns at V<sub>CC</sub> = 5V,  $C_L = 15 pF$ ,  $T_A = 25^{\circ}C$
- Fanout (Over Temperature Range)
  - Standard Outputs ..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity: N<sub>IL</sub> = 30%, N<sub>IH</sub> = 30% of V<sub>CC</sub> at V<sub>CC</sub> = 5V

## Description

The CD74HC4002 logic gate utilizes silicon gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The CD74HC4002 logic family is functional as well as pin compatible with the standard 74LS logic family.

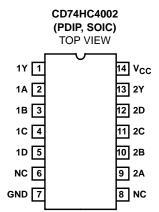
## **Ordering Information**

PART NUMBER	TEMP. RANGE ( <sup>O</sup> C)	PACKAGE	PKG. NO.
CD74HC4002E	-55 to 125	14 Ld PDIP	E14.3
CD74HC4002M	-55 to 125	14 Ld SOIC	M14.15

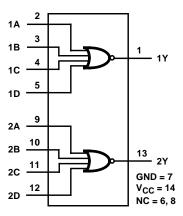
NOTES:

- 1. When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- 2. Die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

## Pinout



# Functional Diagram

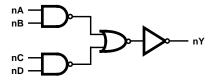


#### TRUTH TABLE

	OUTPUT					
nA	nB	nC	nD	nY		
L	L	L	L	Н		
Н	Х	Х	Х	L		
Х	Н	Х	Х	L		
Х	Х	Н	Х	L		
Х	Х	Х	Н	L		

NOTE: H = High Voltage Level, L = Low Voltage Level, X = Irrelevant

## Logic Symbol



#### **Absolute Maximum Ratings**

DC Supply Voltage, V <sub>CC</sub> 0.5V to 7V
DC Input Diode Current, I <sub>IK</sub>
For V <sub>I</sub> < -0.5V or V <sub>I</sub> > V <sub>CC</sub> + 0.5V
DC Output Diode Current, IOK
For $V_0 < -0.5V$ or $V_0 > V_{CC} + 0.5V$
DC Output Source or Sink Current per Output Pin, IO
For $V_{O} > -0.5V$ or $V_{O} < V_{CC} + 0.5V$
DC V <sub>CC</sub> or Ground Current, I <sub>CC or</sub> I <sub>GND</sub> ±50mA

## **Operating Conditions**

Temperature Range (T <sub>A</sub> )55°C to 125°C
Supply Voltage Range, V <sub>CC</sub>
HC Types
HCT Types4.5V to 5.5V
DC Input or Output Voltage, VI, VO 0V to VCC
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

#### **Thermal Information**

Thermal Resistance (Typical, Note 3)	θ <sub>JA</sub> ( <sup>o</sup> C/W)		
PDIP Package	90		
SOIC Package			
Maximum Junction Temperature	150 <sup>0</sup> C		
Maximum Storage Temperature Range6	5 <sup>o</sup> C to 150 <sup>o</sup> C		
Maximum Lead Temperature (Soldering 10s)			
(SOIC - Lead Tips Only)			

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3.  $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## **DC Electrical Specifications**

		TEST CONDITIONS		v <sub>cc</sub>	25 <sup>0</sup> C		-40 <sup>0</sup> C TO 85 <sup>0</sup> C		-55°C TO 125°C			
PARAMETER	SYMBOL	V <sub>I</sub> (V)	I <sub>O</sub> (mA)	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
High Level Input VIH	-	-	2	1.5	-	-	1.5	-	1.5	-	V	
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	VIL	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	VOH	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output	7		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads		0.02	4.5	-	-	0.1	-	0.1	-	0.1	V	
		0.02	6	-	-	0.1	-	0.1	-	0.1	V	
Low Level Output	1		-	-	-	-	-	-	-	-	-	V
Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
			5.2	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V <sub>CC</sub> or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current (Note)	ICC	V <sub>CC</sub> or GND	0	6	-	-	2	-	20	-	40	μA

NOTE: For dual-supply systems theorectical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

#### Switching Specifications Input tr, tf = 6ns

		TEST		25 <sup>0</sup> C		-40°C TO 85°C	-55°C TO 125°C	
PARAMETER	SYMBOL	CONDITIONS	V <sub>CC</sub> (V)	ТҮР	МАХ	МАХ	MAX	UNITS
HC TYPES					-			
Propagation Delay, nA, nB, nC, nD to nY	<sup>t</sup> PLH, <sup>t</sup> PHL	C <sub>L</sub> = 50pF	2	-	100	125	150	ns
			4.5	-	20	25	30	ns
			6	-	17	21	26	ns
		C <sub>L</sub> = 15pF	5	8	-	-	-	ns
Output Transition Times (Figure 1)	t <sub>TLH</sub> , t <sub>THL</sub>	C <sub>L</sub> = 50pF	2	-	75	95	110	ns
			4.5	-	15	19	22	ns
			6	-	13	16	19	ns
Input Capacitance	C <sub>IN</sub>	-	-	-	10	10	10	pF
Power Dissipation Capacitance	C <sub>PD</sub>	C <sub>L</sub> = 15pF	5	22	-	-	-	pF

NOTES:

4.  $C_{PD}$  is used to determine the dynamic power consumption, per gate.

5.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

## Test Circuit and Waveform

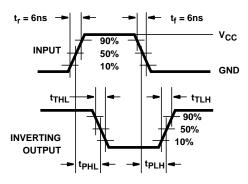


FIGURE 1. HC AND HCU TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

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